

HfO₂ grown with Tetrakis(Dimethylamido)Hafnium (Hf(NMe₂)₄) and H₂O

Growth rates: 1.0A/c@175C, 0.9A/c@200C, 0.94A/c@250C,

Recipe:

precursors: Hf(NMe₂)₄ heated @75C, and H₂O

250C growth:

8=9=250C, 6=7=10=150C, flow=20sccm

pulse H₂O, 0.03s

wait 5s

pulse Hf(NMe₂)₄, 0.3

wait 5s

	Instruction	#	value	▲
0	heater	9	250	
1	heater	8	250	
2	stabilize	9		
3	stabilize	8		
4	pulse	0	0.03	
5	wait		5	
6	pulse	1	0.3	
7	wait		5	
8	goto	4	100	

200C growth:

8=9=200C,6=7=10=150C,flow=20sccm

pulse H₂O, 0.015s

wait 25s

pulse Hf(NMe₂)₄, 0.15

wait 25s

	Instruction	#	value	▲
0	heater	9	200	
1	heater	8	200	
2	stabilize	9		
3	stabilize	8		
4	pulse	0	0.015	
5	wait		25	
6	pulse	1	0.15	
7	wait		25	
8	goto	4	100	

110-175C growth:

8=9= desired set point,6=7=10=150C,flow=20sccm

pulse H₂O, 0.015s

wait 60s

pulse Hf(NMe₂)₄, 0.15

wait 60s

	Instruction	#	value	▲
0	heater	9	175	
1	heater	8	175	
2	stabilize	9		
3	stabilize	8		
4	pulse	0	0.015	
5	wait		60	
6	pulse	1	0.15	
7	wait		60	
8	goto	4	100	